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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104baafp-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

				(5/5)	
Pin count	Package	Fields of Application Note	Ordering Part Number		
80 pins	80-pin plastic LFQFP (12 \times 12 mm, 0.5 mm pitch)	A	R5F104MFAFB#V0, R5F104MGAFB#V0, R5F104MHAFB#V0, R5F104MJAFB#V0		
			R5F104MFAFB#X0, R5F104MGAFB#X0, R5F104MHAFB#X0, R5F104MJAFB#X0		
			R5F104MKAFB#30, R5F104MLAFB#30		
			R5F104MKAFB#50, R5F104MLAFB#50		
		D	R5F104MFDFB#V0, R5F104MGDFB#V0, R5F104MHDFB#V0, R5F104MJDFB#V0		
			R5F104MFDFB#X0, R5F104MGDFB#X0, R5F104MHDFB#X0, R5F104MJDFB#X0		
		G	R5F104MFGFB#V0, R5F104MGGFB#V0, R5F104MHGFB#V0, R5F104MJGFB#V0		
			R5F104MFGFB#X0, R5F104MGGFB#X0, R5F104MHGFB#X0, R5F104MJGFB#X0		
			R5F104MKGFB#30, R5F104MLGFB#30		
			R5F104MKGFB#X0, R5F104MLGFB#50		
	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	A	R5F104MFAFA#V0, R5F104MGAFA#V0, R5F104MHAFA#V0, R5F104MJAFA#V0		
			R5F104MFAFA#X0, R5F104MGAFA#X0, R5F104MHAFA#X0, R5F104MJAFA#X0		
			R5F104MKAFA#30, R5F104MLAFA#30		
			R5F104MKAFA#50, R5F104MLAFA#50		
		D	R5F104MFDFA#V0, R5F104MGDFA#V0, R5F104MHDFA#V0, R5F104MJDFA#V0		
			R5F104MFDFA#X0, R5F104MGDFA#X0, R5F104MHDFA#X0, R5F104MJDFA#X0		
		G	R5F104MFGFA#V0, R5F104MGGFA#V0, R5F104MHGFA#V0, R5F104MJGFA#V0		
			R5F104MFGFA#X0, R5F104MGGFA#X0, R5F104MHGFA#X0, R5F104MJGFA#X0		
			R5F104MKGFA#30, R5F104MLGFA#30		
			R5F104MKGFA#50, R5F104MLGFA#50		
100 pins	100-pin plastic LFQFP (14×14 mm, 0.5 mm pitch)	A	R5F104PFAFB#V0, R5F104PGAFB#V0, R5F104PHAFB#V0, R5F104PJAFB#V0		
			R5F104PFAFB#X0, R5F104PGAFB#X0, R5F104PHAFB#X0, R5F104PJAFB#X0	B#X0	
			R5F104PKAFB#30, R5F104PLAFB#30		
			R5F104PKAFB#50, R5F104PLAFB#50		
		D	R5F104PFDFB#V0, R5F104PGDFB#V0, R5F104PHDFB#V0, R5F104PJDFB#V0		
			R5F104PFDFB#X0, R5F104PGDFB#X0, R5F104PHDFB#X0, R5F104PJDFB#X0		
		G	R5F104PFGFB#V0, R5F104PGGFB#V0, R5F104PHGFB#V0, R5F104PJGFB#V0		
			R5F104PFGFB#X0, R5F104PGGFB#X0, R5F104PHGFB#X0, R5F104PJGFB#X0		
			R5F104PKGFB#30, R5F104PLGFB#30		
			R5F104PKGFB#50, R5F104PLGFB#50		
	100-pin plastic LQFP	A	R5F104PFAFA#V0, R5F104PGAFA#V0, R5F104PHAFA#V0, R5F104PJAFA#V0		
			R5F104PFAFA#X0, R5F104PGAFA#X0, R5F104PHAFA#X0, R5F104PJAFA#X0		
			R5F104PKAFA#30, R5F104PLAFA#30		
			R5F104PKAFA#50, R5F104PLAFA#50		
		D	R5F104PFDFA#V0, R5F104PGDFA#V0, R5F104PHDFA#V0, R5F104PJDFA#V0		
			R5F104PFDFA#X0, R5F104PGDFA#X0, R5F104PHDFA#X0, R5F104PJDFA#X0		
		G	R5F104PFGFA#V0, R5F104PGGFA#V0, R5F104PHGFA#V0, R5F104PJGFA#V0		
			R5F104PFGFA#X0, R5F104PGGFA#X0, R5F104PHGFA#X0, R5F104PJGFA#X0		
			R5F104PKGFA#30, R5F104PLGFA#30		
			R5F104PKGFA#50, R5F104PLGFA#50		
		•	1		

Note Caution

For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14.

on The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.3 36-pin products

• 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



Bottom View						
	0	0	0	0	\Box	
0	0	Ο	Ο	0	0	
0	Ο	0	0	0	0	
0	\bigcirc	Ο	Ο	Ο	0	
0	Ο	0	Ο	Ο	0	
\Box	0	0	0	0	\square	
F	Е	D	С	В	A	

	А	В	С	D	E	F	
6	P60/SCLA0	Vdd	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	6
5	P62/SSI00	P61/SDAA0	Vss	REGC	RESET	P120/ANI19/ VCOUT0 Note	5
4	P72/SO21	P71/SI21/ SDA21	P14/RxD2/SI20/ SDA20/TRDIOD0/ (SCLA0)	P31/TI03/TO03/ INTP4/PCLBUZ0/ (TRJIO0)	P00/TI00/TxD1/ TRGCLKA/ (TRJO0)	P01/TO00/ RxD1/TRGCLKB/ TRJIO0	4
3	P50/INTP1/ SI00/RxD0/ TOOLRxD/ SDA00/TRGIOA/ (TRJO0)	P70/SCK21/ SCL21	P15/PCLBUZ1/ SCK20/SCL20/ TRDIOB0/ (SDAA0)	P22/ANI2/ ANO0 ^{Note}	P20/ANI0/ AVREFP	P21/ANI1/ AVREFM	3
2	P30/INTP3/ SCK00/SCL00/ TRJO0	P16/TI01/TO01/ INTP5/TRDIOC0/ IVREF0 Note/ (RXD0)	P12/SO11/ TRDIOB1/ IVREF1 ^{Note}	P11/SI11/ SDA11/ TRDIOC1	P24/ANI4	P23/ANI3/ ANO1 ^{Note}	2
1	P51/INTP2/ SO00/TxD0/ TOOLTxD/ TRGIOB	P17/TI02/TO02/ TRDIOA0/ TRDCLK/ IVCMP0 Note/ (TXD0)	P13/TxD2/ SO20/TRDIOA1/ IVCMP1 Note	P10/SCK11/ SCL11/ TRDIOD1	P147/ANI18/ VCOUT1 ^{Note}	P25/ANI5	1
	A	B	C	D	E	F	

Note Mounted on the 96 KB or more code flash memory products.

Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

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1.5.7 52-pin products



Note Mounted on the 96 KB or more code flash memory products.



[44-pin, 48-pin, 52-pin, 64-pin products (code flash memory 16 KB to 64 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

					(1/2)			
		44-pin	48-pin	52-pin	64-pin			
	Item	R5F104Fx	R5F104Gx	R5F104Jx	R5F104Lx			
		(x = A, C to E)	(x = A, C to E)	(x = C to E)	(x = C to E)			
Code flash men	nory (KB)	16 to 64	16 to 64	32 to 64	32 to 64			
Data flash mem	ory (KB)	4	4	4	4			
RAM (KB)		2.5 to 5.5 Note	2.5 to 5.5 Note	4 to 5.5 Note	4 to 5.5 Note			
Address space		1 MB						
Main system	High-speed system	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK)						
clock	clock	HS (high-speed main) mode: 1 to 20 MHz ($VDD = 2.7$ to 5.5 V),						
		HS (high-speed main) mode: 1 to 16 MHz ($VDD = 2.4$ to 5.5 V),						
		LS (low-speed main) m	node: 1 to 8 MHz (Vc	D = 1.8 to 5.5 V),				
		LV (low-voltage main) i	mode: 1 to 4 MHz (VD	D = 1.6 to 5.5 V)				
	High-speed on-chip	HS (high-speed main)	mode: 1 to 32 MHz (V	DD = 2.7 to 5.5 V),				
	oscillator clock (fiH)	HS (high-speed main)	mode: 1 to 16 MHz (V	DD = 2.4 to 5.5 V),				
		LS (low-speed main) m	node: 1 to 8 MHz (VD	D = 1.8 to 5.5 V),				
		LV (low-voltage main)	mode: 1 to 4 MHz (VD	D = 1.6 to 5.5 V)				
Subsystem cloc	:k	XT1 (crystal) oscillation	n, external subsystem o	lock input (EXCLKS) 32	2.768 kHz			
Low-speed on-c	chip oscillator clock	15 kHz (TYP.): VDD = 1.6 to 5.5 V						
General-purpos	e register	8 bits \times 32 registers (8	bits \times 8 registers \times 4 ba	inks)				
Minimum instruction execution time		0.03125 μs (High-spee	ed on-chip oscillator clo	ck: fiн = 32 MHz operat	ion)			
		0.05 μs (High-speed sy	ystem clock: fmx = 20 M	IHz operation)				
		30.5 µs (Subsystem cl	оск: fsuв = 32.768 kHz	operation)				
Instruction set		Data transfer (8/16 bi	its)					
		Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits 16 bits × 16 bits)						
		• Multiplication (8 bits \times 8 bits, 16 bits \times 16 bits), Division (16 bits \div 16 bits, 32 bits \div 32 bits)						
		 Multiplication and Accumulation (16 bits × 16 bits + 32 bits) Botato, barrel shift, and bit manipulation (Set, reset, test, and Boolean exercises), etc. 						
I/O port	Total	40	44	48	58			
"o port	CMOS I/O	31		38	48			
		5	5	5	5			
	CMOS output	_	1	1	1			
	N-ch open-drain I/O	4	4	4	4			
	(6 V tolerance)	7	7	7	7			
Timer	16-bit timer	8 channels			1			
		(TAU: 4 channels, Time	er RJ: 1 channel, Timer	RD: 2 channels, Timer	RG: 1 channel)			
	Watchdog timer	1 channel						
	Real-time clock	1 channel						
	(RTC)							
	12-bit interval timer	1 channel						
	Timer output	Timer outputs: 13 char	inels					
		PWM outputs: 9 channels						
	RTC output	1						
		• 1 Hz (subsystem cloc	ck: fsuв = 32.768 kHz)					

(Note is listed on the next page.)

RENESAS

2.1 **Absolute Maximum Ratings**

Absolute Maximum Ratings

Absolute Maximum R	atings			(1/2)
Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		-0.5 to +6.5	V
	EVDD0, EVDD1	EVDD0 = EVDD1	-0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	VI1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	-0.3 to EVDD0 +0.3 and -0.3 to VDD +0.3 Note 2	V
	Vı2	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to VDD +0.3 Note 2	V
Output voltage	Vo1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	-0.3 to EVDD0 +0.3 and -0.3 to VDD +0.3 Note 2	V
	Vo2	P20 to P27, P150 to P156	-0.3 to VDD +0.3 Note 2	V
Analog input voltage	Vai1	ANI16 to ANI20	-0.3 to EVDD0 +0.3 and -0.3 to AVREF(+) +0.3 Notes 2, 3	V
	VAI2	ANI0 to ANI14	-0.3 to VDD +0.3 and -0.3 to AVREF(+) +0.3 ^{Notes 2, 3}	v

Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Must be 6.5 V or lower.

Note 3. Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Remark 2. AVREF (+): + side reference voltage of the A/D converter.

Remark 3. Vss: Reference voltage



Items	Symbol	Conditions	3	MIN.	TYP.	MAX.	Unit
Input voltage, high	Vih1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0.8 EVddo		EVddo	V
	Vih2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55,	TTL input buffer $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	2.2		EVDD0	V
		P80, P81, P142, P143	TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	2.0		EVDD0	V
			TTL input buffer $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}$	1.5		EVDD0	V
	Vінз	P20 to P27, P150 to P156	0.7 Vdd		Vdd	V	
	VIH4	P60 to P63	0.7 EVDD0		6.0	V	
	Vih5	P121 to P124, P137, EXCLK, EX	0.8 Vdd		Vdd	V	
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0		0.2 EVDD0	V
	VIL2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55,	TTL input buffer $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	0		0.8	V
		P80, P81, P142, P143	TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer 1.6 V ≤ EVpp₀ < 3.3 V	0		0.32	V
	VIL3	P20 to P27, P150 to P156		0		0.3 Vdd	V
	VIL4	P60 to P63		0		0.3 EVDD0	V
	VIL5	P121 to P124, P137, EXCLK, EX	CLKS, RESET	0		0.2 Vdd	V

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

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Caution The maximum value of VIH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 is EVDD0, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Items	Symbol	Conditio	ons	MIN.	TYP.	MAX.	Unit
Timer RD input high-level	tтdiн,	TRDIOA0, TRDIOA1, TRDIOE	B0, TRDIOB1,	3/fclk			ns
width, low-level width	t⊤dil	TRDIOC0, TRDIOC1, TRDIOI	D0, TRDIOD1				
Timer RD forced cutoff signal	t TDSIL	Р130/INTP0 2MHz < fclк ≤ 32 MHz		1			μs
input low-level width			$f_{CLK} \leq 2 \ MHz$	1/fclk + 1			
Timer RG input high-level	tтgiн,	TRGIOA, TRGIOB		2.5/fclk			ns
width, low-level width	t⊤gi∟						
TO00 to TO03,	fто	HS (high-speed main) mode	$4.0~V \leq EV_{DD0} \leq 5.5~V$			16	MHz
TO10 to TO13,			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 4.0 \text{ V}$			8	MHz
TRJIOU, TRJOU, TRDIOA0, TRDIOA1			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			4	MHz
TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB output frequency			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			2	MHz
		LS (low-speed main) mode	$1.8 \text{ V} \leq EV \text{DD0} \leq 5.5 \text{ V}$			4	MHz
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			2	MHz
		LV (low-voltage main) mode	$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$			2	MHz
PCLBUZ0, PCLBUZ1 output	f PCL	HS (high-speed main) mode	$4.0~V \leq EV_{DD0} \leq 5.5~V$			16	MHz
frequency			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}$			8	MHz
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			4	MHz
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			2	MHz
		LS (low-speed main) mode	$1.8 \text{ V} \leq EV \text{DD0} \leq 5.5 \text{ V}$			4	MHz
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			2	MHz
		LV (low-voltage main) mode	$1.8 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}$			4	MHz
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			2	MHz
Interrupt input high-level	tinth,	INTP0	$1.6~V \le V_{DD} \le 5.5~V$	1			μs
width, low-level width	tintl	INTP1 to INTP11	$1.6~V \le EV_{DD0} \le 5.5~V$	1			μs
Key interrupt input low-level	t KR	KR0 to KR7	$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	250			ns
width			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$	1			μs
RESET low-level width	trsl			10			μs

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/2)



AC Timing Test Points



External System Clock Timing



TI/TO Timing





TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB



Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remark 1. Rb[Ω]: Communication line (SDAr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance

- **Remark 2.** r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 3 to 5, 14),
 - h: POM number (h = 0, 1, 3 to 5, 7, 14)
- Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/2)

Parameter	Symbol	Conditions		ions HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		transmission	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V \end{array} \end{array} \label{eq:varphi}$		Note 1		Note 1		Note 1	bps
			$\label{eq:constraint} \begin{array}{l} Theoretical value of the \\ maximum transfer rate \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 1.4 \mbox{ k}\Omega, \\ V_b = 2.7 \mbox{ V} \end{array}$		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$		Note 3		Note 3		Note 3	bps
			$\label{eq:constraint} \begin{array}{l} Theoretical value of the \\ maximum transfer rate \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 2.7 \mbox{ k}\Omega, \\ V_b = 2.3 \mbox{ V} \end{array}$		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \end{array}$		Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $4.0 \text{ V} \le \text{EV}\text{DD0} \le 5.5 \text{ V}$ and $2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V}$

1

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{|\text{Transfer rate} \times 2|} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{|V_b|})\}}{(\frac{1}{|\text{Transfer rate}|}) \times \text{Number of transferred bits}}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EVDD0 < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides



RL78/G14

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү1	tксү1 ≥ 2/fc∟к	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 20 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	200		1150		1150		ns
			$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ C_{b} = 20 \; pF, \; R_{b} = 2.7 \; k\Omega \end{array}$	300		1150		1150		ns
SCKp high-level width	tкнı	$\begin{array}{l} 4.0 \ V \leq EV_{DDO} \\ 2.7 \ V \leq V_b \leq 4 \\ C_b = 20 \ pF, \ R_b \end{array}$	o ≤ 5.5 V, .0 V, = 1.4 kΩ	tkcy1/2 - 50		tkcy1/2 - 50		tkcy1/2 - 50		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} \\ 2.3 \ V \leq V_{b} \leq 2 \\ C_{b} = 20 \ pF, \ R_{b} \end{array}$	< 4.0 V, 2.7 V, = 2.7 kΩ	tксү1/2 - 120		tксү1/2 - 120		tксү1/2 - 120		ns
SCKp low-level width	tĸ∟ı	$\begin{array}{l} 4.0 \ V \leq EV_{DDO} \\ 2.7 \ V \leq V_{b} \leq V \\ C_{b} = 20 \ pF, \ R_{b} \end{array}$	o ≤ 5.5 V, 4.0 V, = 1.4 kΩ	tксү1/2 - 7		tксү1/2 - 50		tkcy1/2 - 50		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} \\ 2.3 \ V \leq V_{b} \leq 1 \\ C_{b} = 20 \ pF, \ R_{b} \end{array}$	< 4.0 V, 2.7 V, = 2.7 kΩ	tксү1/2 - 10		tkcy1/2 - 50		tkcy1/2 - 50		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsiк1	$\begin{array}{l} 4.0 \ V \leq EV_{DDO} \\ 2.7 \ V \leq V_{b} \leq V_{b} \\ C_{b} = 20 \ pF, \ R_{b} \end{array}$	0 ≤ 5.5 V, 4.0 V, = 1.4 kΩ	58		479		479		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} \\ 2.3 \ V \leq V_{b} \leq \\ C_{b} \texttt{=} 20 \ pF, \ R_{b} \end{array}$	< 4.0 V, 2.7 V, = 2.7 kΩ	121		479		479		ns
SIp hold time (from SCKp↑) ^{Note 1}	tĸsı1	$\begin{array}{l} 4.0 \ V \leq EV_{DDO} \\ 2.7 \ V \leq V_{b} \leq V_{b} \\ C_{b} \texttt{=} 20 \ pF, \ R_{b} \end{array}$	0 ≤ 5.5 V, 4.0 V, = 1.4 kΩ	10		10		10		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} \\ 2.3 \ V \leq V_{b} \leq 1 \\ C_{b} = 20 \ pF, \ R_{b} \end{array}$	< 4.0 V, 2.7 V, = 2.7 kΩ	10		10		10		ns
Delay time from SCKp↓ to SOp out- put ^{Note 1}	tkso1	$\begin{array}{l} 4.0 \ V \leq EV_{DD}\\ 2.7 \ V \leq V_{b} \leq V\\ C_{b} = 20 \ pF, \ R_{b} \end{array}$	0 ≤ 5.5 V, 4.0 V, = 1.4 kΩ		60		60		60	ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} \\ 2.3 \ V \leq V_{b} \leq \\ C_{b} = 20 \ pF, \ R_{b} \end{array}$	< 4.0 V, 2.7 V, = 2.7 kΩ		130		130		130	ns

(TA = -40 to +85°C, 2.7 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(Notes, Caution, and Remarks are listed on the next page.)



- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. Use it with $EVDD0 \ge Vb$.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin, and the N-ch open drain output (Vbb tolerance (for the 30- to 52-pin products)/EVbb tolerance (for the 64- to 100-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For ViH and ViL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



- **Remark 1.** Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
- Remark 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.
 Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.



2.5.2 Serial interface IICA

(1) I²C standard mode

```
(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)
```

Parameter	Symbol	Conditions		HS (high-sp mc	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock	fscL	Standard mode:	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	0	100	0	100	0	100	kHz
frequency		fc∟k ≥ 1 MHz	$1.8~V \le EV_{DD0} \le 5.5~V$	0	100	0	100	0	100	kHz
			$1.7~V \leq EV_{DD0} \leq 5.5~V$	0	100	0	100	0	100	kHz
			$1.6~V \leq EV_{DD0} \leq 5.5~V$	-	_	0	100	0	100	kHz
Setup time of	tsu: STA	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	4.7		4.7		4.7		μs
restart condition		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		4.7		4.7		4.7		μs
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		4.7		4.7		4.7		μs
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		-	_	4.7		4.7		μs
Hold time Note 1	thd: STA	$2.7 \text{ V} \leq EV_{DD0} \leq 8$	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			4.0		4.0		μs
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	4.0		4.0		4.0		μs
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	4.0		4.0		4.0		μs
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		-	_	4.0		4.0		μs
Hold time when	tLOW	$2.7 \text{ V} \leq EV_{DD0} \leq 8$	5.5 V	4.7		4.7		4.7		μs
SCLA0 = "L"		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			4.7		4.7		μs
		$1.7 \text{ V} \leq EV_{DD0} \leq 8$	$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			4.7		4.7		μs
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	-	_	4.7		4.7		μs
Hold time when	tніgн	$2.7 \text{ V} \leq EV_{DD0} \leq 8$	5.5 V	4.0		4.0		4.0		μs
SCLA0 = "H"		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	4.0		4.0		4.0		μs
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	4.0		4.0		4.0		μs
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	-	_	4.0		4.0		μs

 $(\ensuremath{\textit{Notes}}, \ensuremath{\textit{Caution}}, \ensuremath{\text{and}} \ensuremath{\textit{Remark}}$ are listed on the next page.)



2.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +85°C	, 1.8 V \leq EVDD0 =	$EVDD1 \leq VDD \leq 5.5 V$, $Vss = EVsso = EVss1 = 0 V$)
--------------------	------------------------	-----------------------------	---------------------------------

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	thd	POR and LVD reset must end before the external reset ends.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the external reset ends).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit. The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends

tHD: How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0.8 EVDD0		EVddo	V
	VIH2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55,	TTL input buffer $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	2.2		EVDD0	V
		P80, P81, P142, P143	TTL input buffer $3.3 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	2.0		EVDD0	V
			TTL input buffer 2.4 V ≤ EVDD0 < 3.3 V	1.5		EVDD0	V
	Vінз	P20 to P27, P150 to P156	·	0.7 Vdd		Vdd	V
	VIH4	P60 to P63		0.7 EVDD0		6.0	V
	Vih5	P121 to P124, P137, EXCLK, EX	P121 to P124, P137, EXCLK, EXCLKS, RESET			Vdd	V
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0		0.2 EVDD0	V
	VIL2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55,	TTL input buffer $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	0		0.8	V
		P80, P81, P142, P143	TTL input buffer $3.3 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer 2.4 V ≤ EVDD0 < 3.3 V	0		0.32	V
	VIL3	P20 to P27, P150 to P156		0		0.3 VDD	V
	VIL4	P60 to P63		0		0.3 EVDD0	V
	VIL5	P121 to P124, P137, EXCLK, EX	CLKS, RESET	0		0.2 VDD	V

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

(3/5)

The maximum value of VIH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 is EVDD0, even in the N-ch open-drain mode.

Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins. Remark

Caution



3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

$(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spee	Unit	
			MIN.	MAX.	
Transfer rate Note 1		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		fмск/12 Note 2	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 3$		2.6	Mbps

Note 1.Transfer rate in the SNOOZE mode is 4800 bps only.
However, the SNOOZE mode cannot be used when FRQSEL4 = 1.Note 2.The following conditions are required for low voltage interface when EVDD0 < VDD.
 $2.4 V \le EVDD0 < 2.7 V$: MAX. 1.3 MbpsNote 3.The maximum operating frequencies of the CPU/peripheral hardware clock (fcLk) are:
HS (high-speed main) mode: 32 MHz (2.7 V $\le VDD \le 5.5 V$)
16 MHz (2.4 V $\le VDD \le 5.5 V$)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14) **Remark 2.** fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))



Parameter	Symbol	Conditions			TYP.	MAX.	Unit
Voltage detection	VLVDD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1, falling reset voltage		2.64	2.75	2.86	V
threshold	VLVDD1	LVIS1, LVIS0 = 1, 0	LVIS1, LVIS0 = 1, 0 Rising release reset voltage		2.92	3.03	V
			Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V
	VLVDD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
			Falling interrupt voltage	3.83	3.98	4.13	V

(2) Interrupt & Reset Mode

(TA = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, VSS = 0 V)

3.6.7 Power supply voltage rising slope characteristics

(TA = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 3.4 AC Characteristics.



R5F104LKAFB, R5F104LLAFB R5F104LKGFB, R5F104LLGFB





4.9 80-pin products

R5F104MFAFB, R5F104MGAFB, R5F104MHAFB, R5F104MJAFB R5F104MFDFB, R5F104MGDFB, R5F104MHDFB, R5F104MJDFB R5F104MFGFB, R5F104MGGFB, R5F104MHGFB, R5F104MJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP80-12x12-0.50	PLQP0080KE-A	P80GK-50-8EU-2	0.53



NOTE

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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